

## TABLE OF CONTENTS

Preface	v
Symposium Information	vii
<b>Part I. Experimental Methods for the Determination of Non-Stoichiometry</b>	
Chemical Composition and Properties of Semiconductors J. Vedel	3
Precise Compositional and Trace-Elemental Analysis by Chemical Methods in Compound Semiconductors M.H. Yang, M.L. Lee and H.L. Hwang	15
Non-Stoichiometry and Aspects of Heavy Doping in GaAs Revealed by X-Ray Quasi-Forbidden Reflection (XFR) Method I. Fujimoto	27
Crystal Quality Control by Means of the Combined Use of X-Ray Diffraction and Ultrasound E. Zolotoyabko	39
<b>Part II. Phase Relations and Point Defect Equilibria</b>	
A Model for the Phase Extent of Gallium Arsenide Derived from Experimental Dopant Solubility Data D.T.J. Hurle	47
Characterization of CuInS <sub>2</sub> by Perturbed Angular Correlations of $\gamma$ Rays M. Brüssler, H. Metzner, K.D. Husemann and H.J. Lewerenz	59

Heat-Treatment of AgGaS <sub>2</sub> Single Crystals in Sulfur Atmosphere Y. Noda, T. Kurasawa, H. Watanabe, Y. Furukawa and K. Matsumoto	63
Defect Structure of Non-Stoichiometric Cu-I-III-VI <sub>2</sub> Chalcopyrite Semiconductors H.Y. Ueng and H.L. Hwang	69
Influence of Annealing Method on Electrical Properties of Hg <sub>1-x</sub> Cd <sub>x</sub> Te E. Belas, P. Höschl, P. Moravec and J. Franc	81
Defect Chemistry and Electrical Properties of Iron-Pyrite (FeS <sub>2-x</sub> ) S. Fiechter, A. Hartmann, P. Dulski, D. Jokisch and H. Tributsch	87
 <b>Part III. Stoichiometry Control in Melt and Solution Growth</b>	
Stoichiometry Control in Compound Semiconductor Crystals J.-I. Nishizawa	95
Modified LEC Technique for Growing High Quality III-V Semiconductors M. Tatsumi, T. Kawase and K. Tada	107
Crystals of CuInSe <sub>2</sub> with Controlled Deviations from Stoichiometry L.S. Yip, W.S. Weng, Z.A. Shukri, I. Shih and C.H. Champness	119
CuInSe <sub>2</sub> Grown Under Elevated Pressures – Part 1: Structural and Defect Characterization M.L. Fearheiley, N. Dietz, S. Schroetter and H.J. Lewerenz	125
CuInSe <sub>2</sub> Grown Under Elevated Pressures – Part 2: Optical Defect Characterization N. Dietz, M.L. Fearheiley and H.J. Lewerenz	133

## Part IV. Stoichiometry Control in Vapor Phase Epitaxy

Stoichiometry Issues in Gallium Nitride and Other Wide Gap Semiconductors J.I. Pankove	143
Quantitative Approach of Non-Stoichiometric Interfaces Following a Growth Interruption Sequence: Application to Lattice-Matched InGaAs/InP Quantum Wells S. Juillaguet, J.P. Laurenti, R. Schwedler, K. Wolter, J. Camassel and H. Kurz	155
Optical Characterization of Strained InGaAs/InP Quantum Well Structures R. Schwedler, B. Gallmann, K. Wolter, Ch. Jaekel, M. Stollenwerk, J. Camassel, J.P. Laurenti, S. Juillaguet and H. Kurz	161
Influence of the InP-Substrate Temperature on the Properties of MBE Grown $\text{Al}_{0.48}\text{In}_{0.52}\text{As}$ Layers E. Tournié, Y.-H. Zhang and K. Ploog	167
A Multi-Mode Capped-Mesa-Buried-Heterostructure Laser Diode (MM-CMBH) with a Reduced Contact and Etched Trench G.C. Chi	173
The Growth Mechanisms and Stoichiometric Properties of GaSb Compounds Grown by MOCVD Y.K. Su, S.M. Chen, H.Y. Ueng and F.S. Juang	179
Microstructure of $\text{SrF}_2$ Epitaxial Layer on InP Semiconductor and of their Interface P.V. Huong, E. Ollier, S. Delavoye, R. Cavagnat, B. Mombelli, A.S. Barrière and A.L. Verma	185

## Part V. Characterization of Specific Point Defects and Complexes

ODMR of Stoichiometry Defects in III-V Semiconductors J.-M. Spaeth, M. Fockele and K. Krambrock	193
Photoluminescence and Transport Investigations in CdTe W. Stadler, F. Wang, R. Schwarz, K. Oettinger, B.K. Meyer, D.M. Hofmann, D. Sinerius and K.W. Benz	205
Effect of Non-Stoichiometry on Near-Bandedge Absorption and Non-Radiative Recombination in Bulk GaAs S. Tüzemen and M.R. Brozel	211
Direct Observation of the Electrical Activity of the EL2 Center in its Metastable Configuration in $\text{Ga}_{1-x}\text{Al}_x\text{As}$ Alloys G. Brémond, G. Guillot, D. Stievenard and R. Azoulay	217
Influence of Melt Stoichiometry on Deep Hole Traps in n-Type LEC Gallium Arsenide G. Marrakchi, A. Kalboussi, G. Guillot, S. Alaya, H. Maaref and R. Forinari	223
Chemical Shift of DX Centers in $\text{Ga}(\text{As}_{1-x}\text{P}_x)$ J.M. Sallese, D.K. Maude, M.L. Fille, U. Willke, J.C. Portal and P. Gibart	229
Post-Implantation Defects and Non-Stoichiometry of I-Implanted ZnSe A. Olszewski, J. Krynicki and R. Groetzschel	237
Photoluminescence of $\text{GaAs}_{1-x}\text{P}_x$ M.S. Feng, H.L. Hsiao and H.L. Hwang	243
Photoluminescence Study of CdTe:Sm Crystals P. Han, W. Shan, T. Zhou, K.J. Ma and S.C. Shen	249

**Part VI. Non-Stoichiometry and Deep Levels in I-III-VI<sub>2</sub> Compounds**

- Stoichiometric Effects on the Properties of Cu Based Chalcopyrite (I,III,VI<sub>2</sub>) Semiconductor Thin Films  
J.J. Loferski 257
- P-d Hybridization of Sulfur Annealed Copper Indium Disulfide  
T.M. Hsu and H.L. Hwang 269
- Chemical and Structural Characterization of Thin Films of CuInSe<sub>2</sub>  
B.H. Tseng and C.A. Wert 275
- DLTS Investigation of the Defect Chemistry of Non-Stoichiometry CuInSe<sub>2</sub>  
H.J. Möller and E. Rodak 281
- Deep Levels in Monocrystalline CuInSe<sub>2</sub>  
L. Li and I. Shih 287

**Part VII. Non-Stoichiometric Oxide Semiconductors**

- Oxide Identification by Photoluminescence  
B. Lefez and M. Lenglet 295
- Correlations Between Structure and Electrical Properties of Tin-Doped Indium Oxide Thin Films:  
An EXAFS Investigation  
Ph. Parent, H. Dexpert, G. Tourillon and J.-M. Grimal 301
- Oxygen Non-Stoichiometry in Thermally Annealed and Hydrogen Implanted TiO<sub>2</sub> Thin Films Observed by Raman Spectroscopy  
A. Turcović, M. Ivanda, J. Tudorić-Ghemo, N. Godinović and I. Sorić 307

Electrical Properties of Doped and Non-stoichiometric $\text{SnO}_{2-\delta}$ and its Stoichiometry Control by Co-Firing with $\text{Sn}_{2-a}^{2+}\text{M}_{2-b}\text{Sn}_b^{4+}\text{O}_{7-a-b/2}$ (M=Ta, Nb)1 G. Behr, G. Krabbes, U. Wiesner, W. Bieger and J. Werner	315
Author Index	321